

BF423 is PNP silicon planar epitaxial transistor designed for high voltage video amplifiers in colour television receivers including grid driver and in driver stages of high voltage line deflection circuits. It is complementary to BF422.

TO-92



ECB

ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	VCBO	250V
Collector-Emitter Voltage	VCEO	250V
Emitter-Base Voltage	VEBO	5V
Collector Current	IC	200mA
Total Power Dissipation	Ptot	830mW
Operating Junction & Storage Temperature	Tj, Tstg	-55 to +150°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Base Breakdown Voltage	BVCBO	250		V	IC=10μA IE=0
Collector-Emitter Breakdown Voltage	BVCEO	250		V	IC=2.5mA IB=0
Emitter-Base Breakdown Voltage	BVEBO	5		V	IE=10μA IC=0
Collector Cutoff Current	ICBO		10	nA	VCB=200V IE=0
Emitter Cutoff Current	IEBO		10	nA	VEB=5V IC=0
D.C. Current Gain	HFE	50			IC=25mA VCE=20V
Current Gain-Bandwidth Product	fT	60		MHz	IC=10mA VCE=10V



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